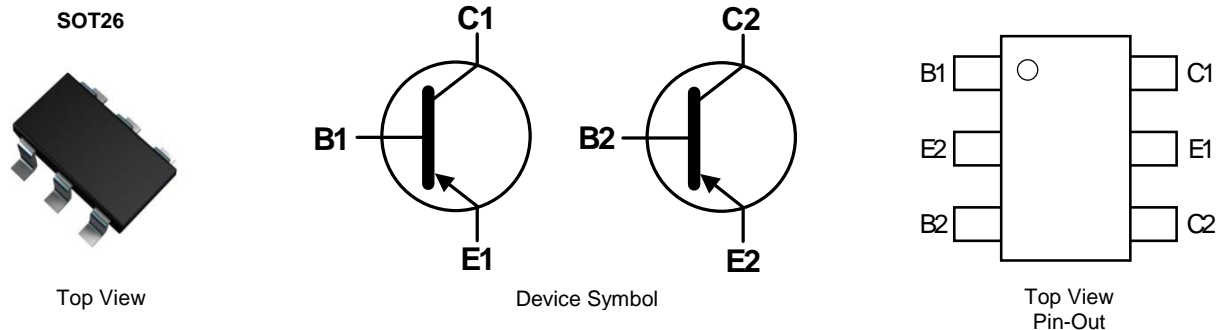


Features

- $BV_{CEO} > -60V$
- $I_{CM} = -1A$ Peak Pulse Current
- General Purpose PNP Transistors Ideally Suited for Low Power Amplification and Switching Applications
- Dual Transistors in a Single SOT26 Package, Taking Half of the Footprint of Two Equivalent Transistors in SOT23
- Epitaxial Planar Die Construction
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 [Ⓔ]
- Weight: 0.015 grams (Approximate)

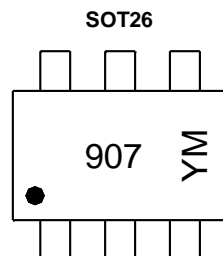


Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMMT2907A-7	AEC-Q101	907	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



907 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: C = 2015)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	I _C	-600	mA
Peak Pulsed Collector Current	I _{CM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

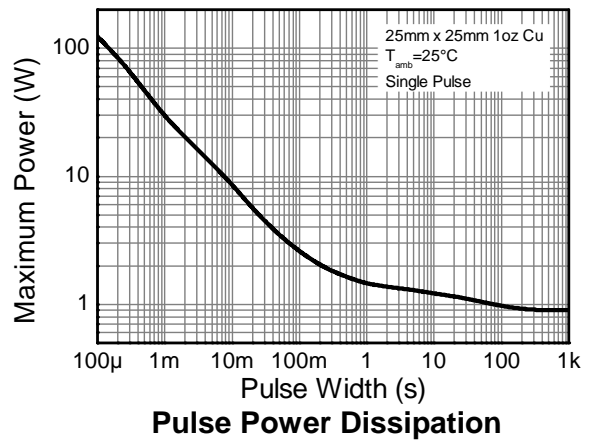
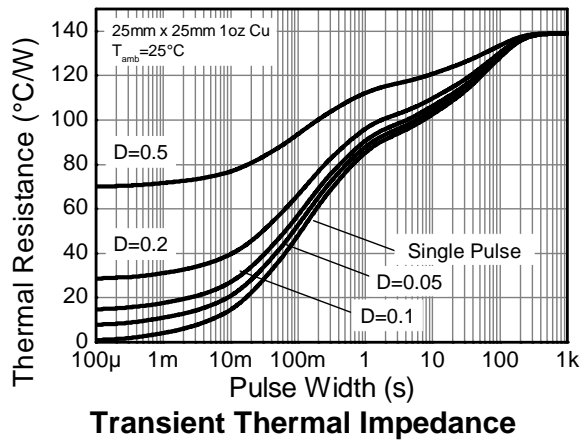
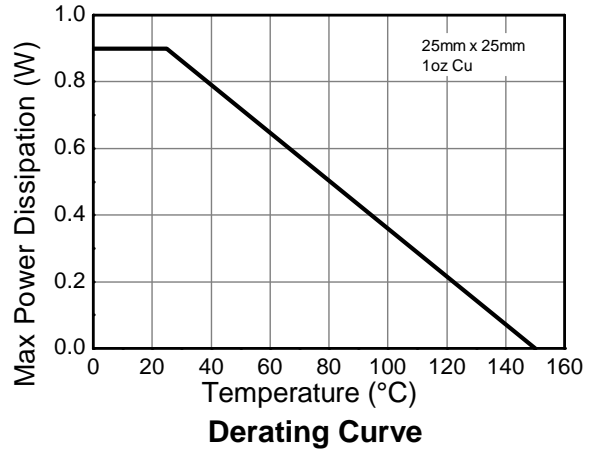
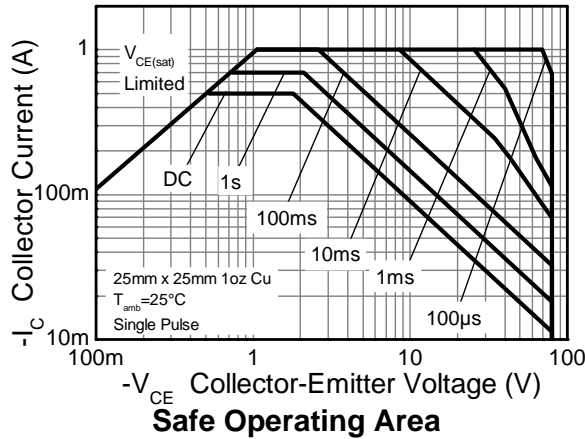
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	1.28	W
		10.3	
Linear Derating Factor		0.90	mW/°C
		7.14	
Thermal Resistance, Junction to Ambient	R _{θJA}	97	°C/W
		140	
Thermal Resistance, Junction to Lead	R _{θJL}	113	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as Note 5, except the device is measured at t ≤ 5 seconds.
 7. For a dual device with one active die.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

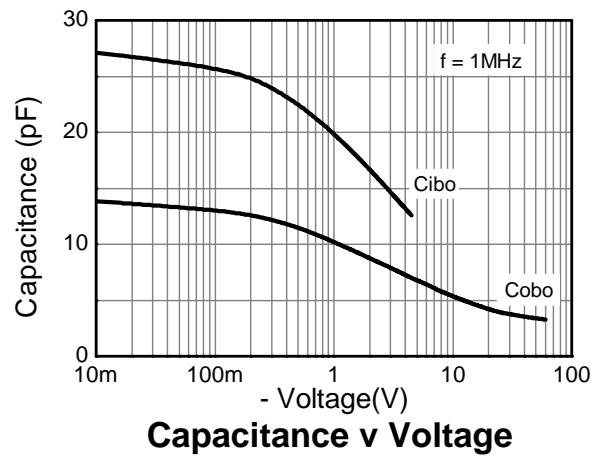
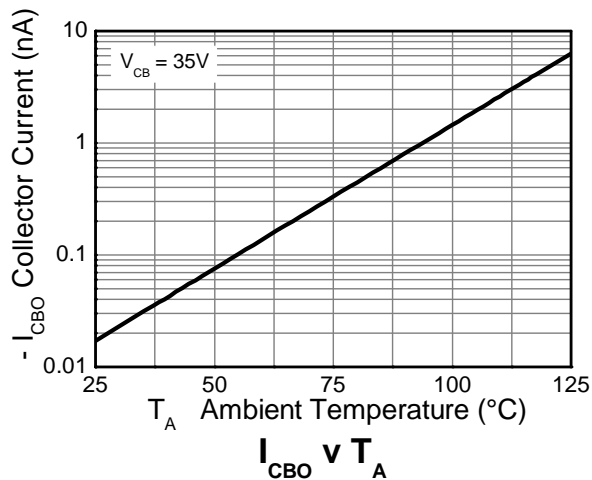
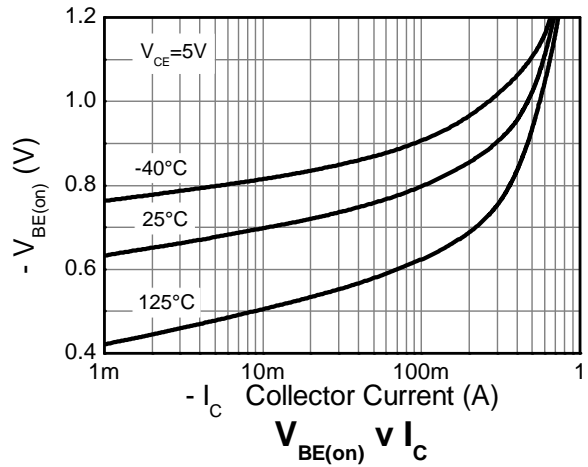
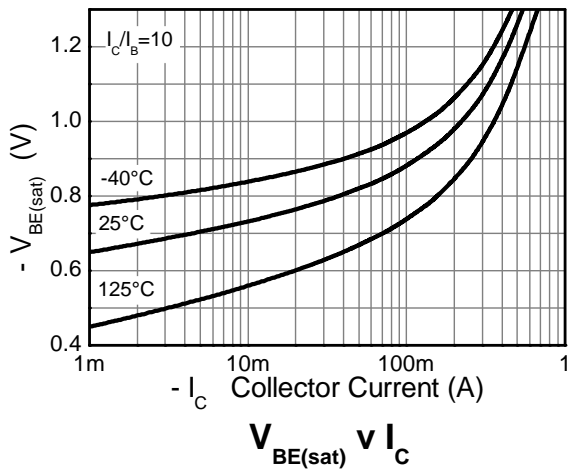
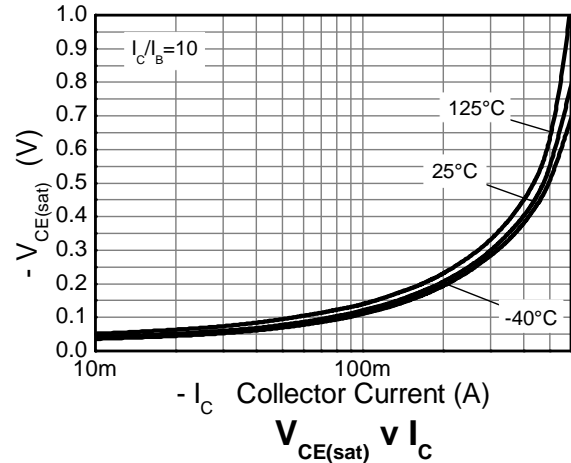
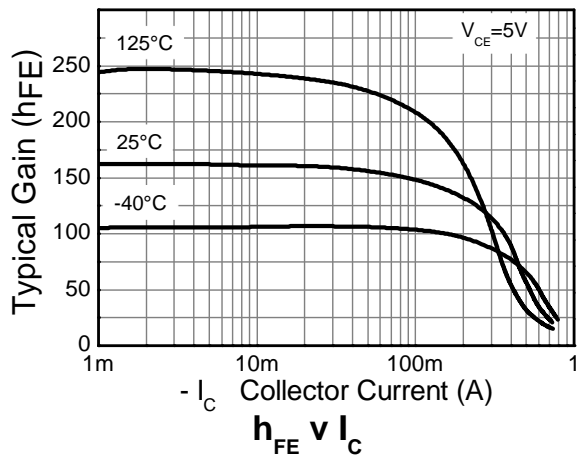


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-60	—	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	-60	—	—	V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector-Base Cut-Off Current	I_{CBO}	—	—	-10	nA	$V_{CB} = -50\text{V}, I_E = 0$
		—	—	-10	μA	$V_{CB} = -50\text{V}, I_E = 0, T_A = +150^\circ\text{C}$
Collector-Emitter Cut-Off Current	I_{CEV}	—	—	± 50	nA	$V_{CE} = -30\text{V}, V_{BE} = \pm 0.25\text{V}$
Base-Emitter Cut-Off Current	I_{BEV}	—	—	± 50	nA	$V_{CE} = -30\text{V}, V_{BE} = \pm 0.25\text{V}$
ON CHARACTERISTICS (Note 10)						
DC Current Gain	h_{FE}	75	—	—	—	$I_C = -100\mu\text{A}, V_{CE} = -10\text{V}$
		100	—	—		$I_C = -1.0\text{mA}, V_{CE} = -10\text{V}$
		100	—	—		$I_C = -10\text{mA}, V_{CE} = -10\text{V}$
		100	—	300		$I_C = -150\text{mA}, V_{CE} = -10\text{V}$
		50	—	—		$I_C = -500\text{mA}, V_{CE} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	-0.4	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$
		—	—	-1.6		$I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	—	-1.3	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$
		—	—	-2.6		$I_C = -500\text{mA}, I_B = -50\text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}	—	5.2	—	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0\text{mA}$
Input Capacitance	C_{ibo}	—	16.3	—	pF	$V_{EB} = -2.0\text{V}, f = 1.0\text{MHz}, I_C = 0\text{mA}$
Current Gain-Bandwidth Product	f_T	200	307	—	MHz	$V_{CE} = -2\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$
Turn-On Time	t_{on}	—	—	21	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$
Delay Time	t_d	—	—	5.5	ns	
Rise Time	t_r	—	—	15.3	ns	
Turn-Off Time	t_{off}	—	—	200	ns	$V_{CC} = -6\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$
Storage Time	t_s	—	—	160	ns	
Fall Time	t_f	—	—	40	ns	

Note: 10. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

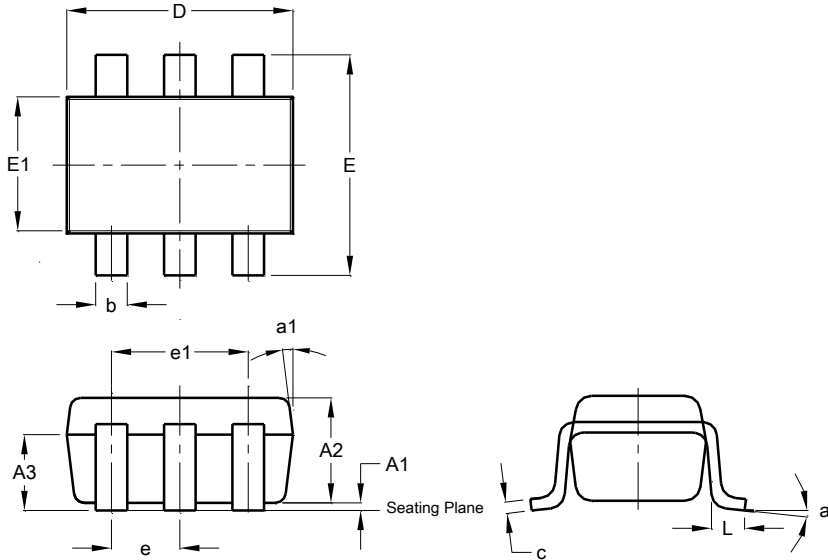
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

SOT26

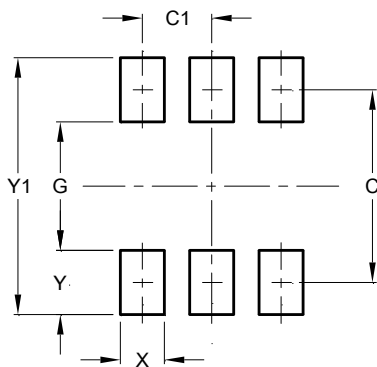


SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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